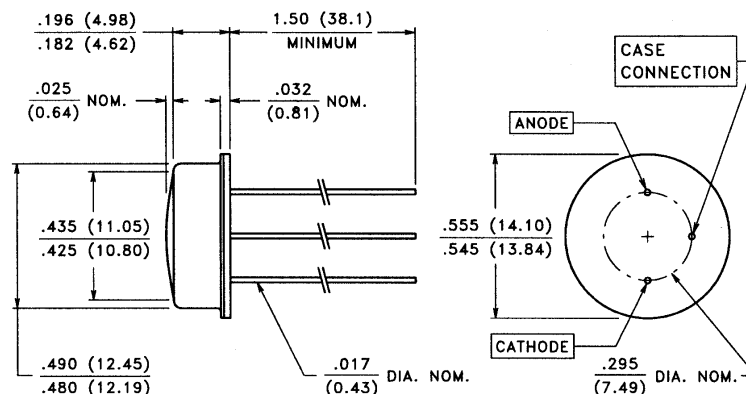


## PACKAGE DIMENSIONS inch (mm)



CASE 15 TO-8 HERMETIC  
CHIP ACTIVE AREA: .058 in<sup>2</sup> (37.7 mm<sup>2</sup>)

## PRODUCT DESCRIPTION

Large area planar silicon photodiode in a "flat" window, three lead TO-8 package. Chip is isolated from case. The third lead allows case to be grounded. These diodes have very high shunt resistance and have good blue response.

## ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -40°C to 110°C  
Operating Temperature: -40°C to 110°C

## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTB curves, pages 21-22)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTB6061J			UNITS
			Min.	Typ.	Max.	
I <sub>SC</sub>	Short Circuit Current	H = 100 fc, 2850 K	260	350		μA
TC I <sub>SC</sub>	I <sub>SC</sub> Temperature Coefficient	2850 K		.12	.23	%/°C
V <sub>OC</sub>	Open Circuit Voltage	H = 100 fc, 2850 K		490		mV
TC V <sub>OC</sub>	V <sub>OC</sub> Temperature Coefficient	2850 K		-2.0		mV/°C
I <sub>D</sub>	Dark Current	H = 0, V <sub>R</sub> = 2.0 V			2.0	nA
R <sub>SH</sub>	Shunt Resistance	H = 0, V = 10 mV		.10		GΩ
TC R <sub>SH</sub>	R <sub>SH</sub> Temperature Coefficient	H = 0, V = 10 mV		-8.0		%/°C
C <sub>J</sub>	Junction Capacitance	H = 0, V = 0		8.0		nF
S <sub>R</sub>	Sensitivity	365 nm		0.1		A/W
λ <sub>range</sub>	Spectral Application Range		320		1100	nm
λ <sub>p</sub>	Spectral Response - Peak			920		nm
V <sub>BR</sub>	Breakdown Voltage		2	40		V
θ <sub>1/2</sub>	Angular Resp. - 50% Resp. Pt.			±55		Degrees
NEP	Noise Equivalent Power			5.7 x 10 <sup>-14</sup> (Typ.)		W/√Hz
D*	Specific Detectivity			1.1 x 10 <sup>13</sup> (Typ.)		cm√Hz / W